

(2-92)

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>3025.1US (95-1003.1)</b>		Application Number <del>Not Yet Assigned</del> <b>09/506,204</b>	
				Applicant <b>Trung T. Doan</b>		Filing Date <b>February 17, 2000</b>	
				Group Art Unit <del>Unknown</del> <b>2811</b>			

  

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TH	5,355,020	10/11/94	Lee et al.	257	741	
TH	5,512,512	04/30/96	Isobe			

  

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

  

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
TH		Dixit et al., "A Novel High Pressure Low Temperature Aluminum Plug Technology For Sub-0.5 $\mu$ m Contact/Via Geometries", <u>IEDM</u> , pp. <del>105-108, 1994.</del> <b>Dec. 1994, pp. 105-108</b>
TH		Dixit et al., "A Novel 0.25 $\mu$ m Via Plug Process Using Low Temperature CVD Al/TiN", <u>IEDM</u> <del>95, pp. 1001-1003.</del> <b>Dec. 1995, pp. 1001-1003.</b>
TH		Dixit et al., "A reactively sputtered coherent TiN process for sub-0.5 $\mu$ m technology", <u>SPIE</u> , Vol. 2090 Multilevel Interconnection; pp. 12-21, 1993.
TH		Dixit et al., "An Integrated Low Resistance Aluminum Plug and Low-k Polymer Dielectric For High Performance 0.25 $\mu$ m Interconnects", <u>1996 Symposium on VLSI Technology Digest of Technical Papers</u> , pp. 86-87, 1996.
TH		Dixit et al., "Application of High Pressure Extruded Aluminum to ULSI Metallization", <u>Semiconductor International</u> , pp. 79-85, August 1995.
TH		Jain et al., "Chemical mechanical planarization of multilayer dielectric stacks", <u>SPIE</u> , Vol. 2335, pp. 2-11, <b>1993.</b>
TH		Mizobuchi et al., "Application of Force Fill Al-Plug Technology to 64Mb DRAM and 0.35 $\mu$ m Logic", <u>1995 Symposium on VLSI Technology Digest of Technical Papers</u> , 45-46.
TH		Ting et al., "Effect of Via Etch Profile and Barrier Metal on Electromigration Performance of W-filled Via Structure in TiN/AlCu/TiN Metallization", <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 391, pp. 453-458, 1995.

  

EXAMINER <div style="text-align: center; font-size: 1.5em;">Guach</div>	DATE CONSIDERED <div style="text-align: center; font-size: 1.5em;">11/03/2000</div>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.